

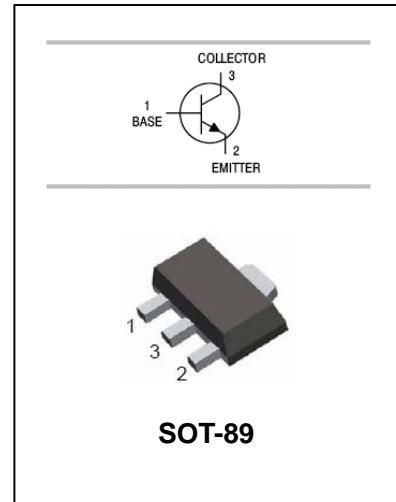


# NPN Silicon Epitaxial Planar Transistor

# CXT5551

## FEATURES

- Switching and amplification in high voltage.
- Low current(max. 600mA)
- High voltage (max. 180V)



## APPLICATIONS

- High voltage amplifier application.

## ORDERING INFORMATION

Type No.	Marking	Package Code
CXT5551	1G6	SOT-89

## MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	180	V
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current -Continuous	600	mA
P <sub>C</sub>	Collector Dissipation	0.625	W
R <sub>θJA</sub>	Thermal resistance	250	°C/W
T <sub>j</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-65 to +150	°C



NPN Silicon Epitaxial Planar Transistor

**CXT5551**

**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	180		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1.0mA, I_B=0$	160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=120V, I_E=0$		50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4V, I_C=0$		50	nA
DC current gain	$h_{FE}$	$V_{CE} = 5V; I_C = 1mA$ $V_{CE} = 5V; I_C = 10mA$ $V_{CE} = 5V; I_C = 50mA$	80 100 30	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B= 1mA$ $I_C=50mA, I_B= 5mA$		0.15 0.20	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B= 1mA$ $I_C=50mA, I_B= 5mA$		1.0 1.0	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C= 10mA,$ $f=100MHz$	100	300	MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		6.0	pF
Small-signal current gain	$h_{fe}$	$I_C=1mA, V_{CE}=10V,$ $f=1.0kHz$	50	200	
Noise Figure	NF	$I_C=200\mu A, V_{CE}=5V,$ $f=10-15.7kHz, R_S=1.0\Omega$		8	dB



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TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

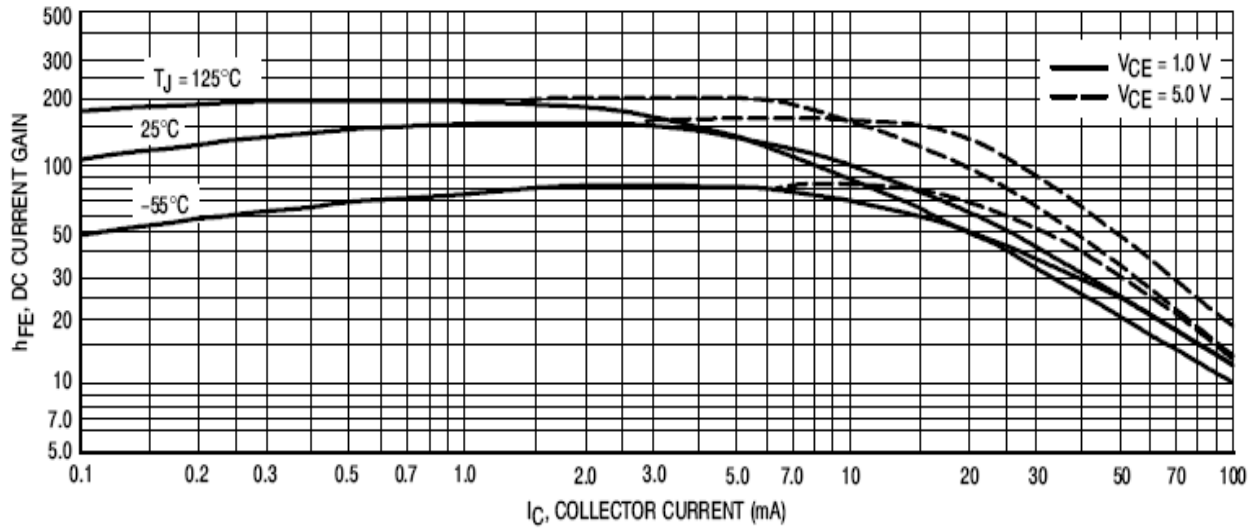


Figure 1. DC Current Gain

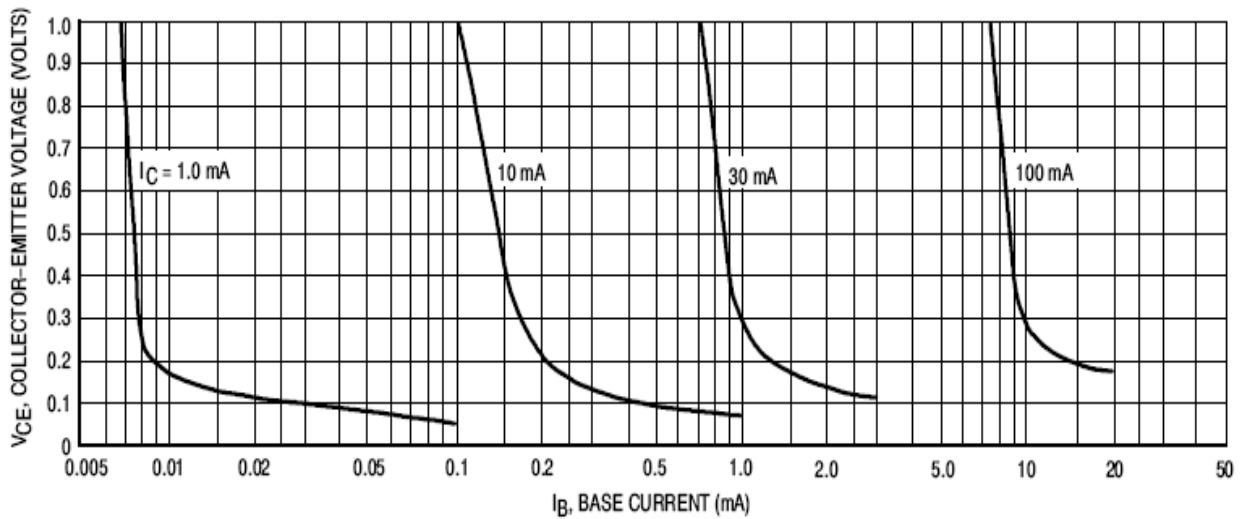


Figure 2. Collector Saturation Region



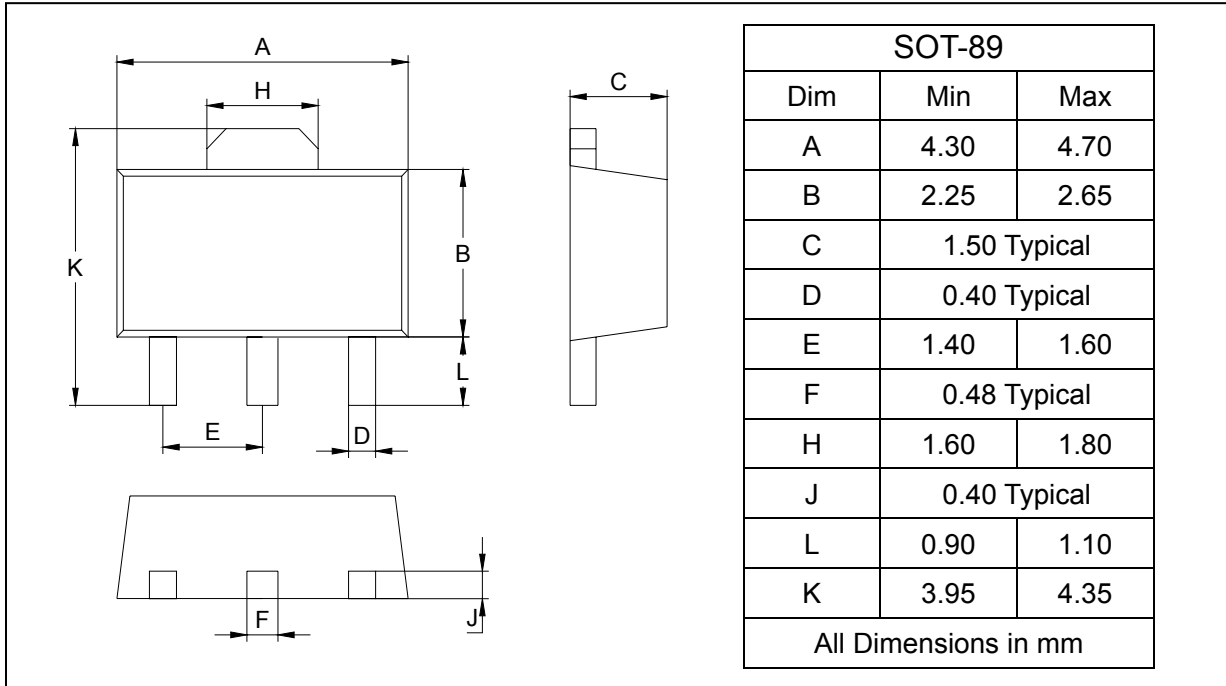
**NPN Silicon Epitaxial Planar Transistor**

**CXT5551**

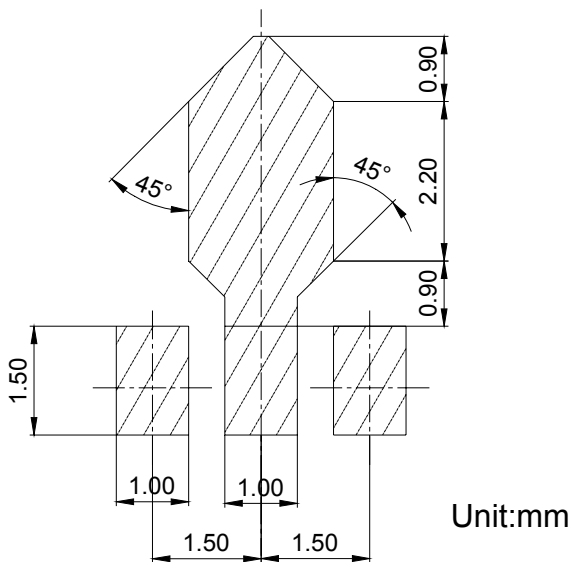
**PACKAGE OUTLINE**

Plastic surface mounted package

SOT-89



**SOLDERING FOOTPRINT**



**PACKAGE INFORMATION**

Device	Package	Shipping
CXT5551	SOT-89	1000/Tape&Reel